

74VHC541 Octal Buffer/Line Driver with TRI-STATE® Outputs

General Description

The VHC541 is an advanced high-speed CMOS device fabricated with silicon gate CMOS technology. It achieves the high-speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The VHC541 is an octal buffer/line driver designed to be employed as memory and address drivers, clock drivers and bus oriented transmitter/receivers.

This device is similar in function to the VHC244 while providing flow-through architecture (inputs on opposite side from outputs). This pinout arrangement makes this device especially useful as an output port for microprocessors, allowing ease of layout and greater PC board density.

An input protection circuit insures that 0V to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery backup. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- Low power dissipation: $I_{CC} =$ 4 μA (max) at $T_A =$ 25°C
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- All inputs are equipped with a power down protection function
- \blacksquare Balanced propagation delays: $t_{PLH} \cong t_{PHL}$
- Low noise: V_{OLP} = 0.9V (typ) ✓
- Pin and function compatible with 74HC541

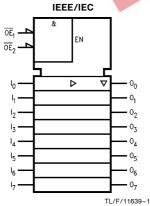
Commercial	Package Number	Package Description
74VHC541M	M20B	20-Lead Molded JEDEC SOIC
74VHC541SJ	M20D	20-Lead Molded EIAJ SOIC
74VHC541MTC	MTC20	20-Lead Molded JEDEC Type 1 TSSOP
74VHC541N	N20A	20-Lead Molded DIP

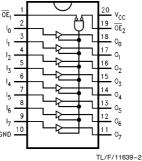
Note: Surface mount packages are also available on Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Logic Symbol

Connection Diagram

Pin Assignment for DIP, **TSSOP and SOIC**





Truth Table

	Outputs					
ŌĒ ₁	\overline{OE}_2	ı	Outputs			
L	L	Н	Н			
Н	Χ	X	Z			
Х	Н	X	Z			
L	L	L	L			

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = High Impedance

Absolute Maximum Ratings (Note 1)

Supply Voltage (V_{CC}) -0.5V to +7.0VDC Input Voltage (V_{IN}) -0.5V to +7.0VDC Output Voltage (V_{OUT}) - 0.5V to V $_{\mbox{\scriptsize CC}}$ + 0.5V Input Diode Current (I_{IK}) -20 mA Output Diode Current (I_{OK}) $\pm\,20~mA$ DC Output Current (I_{OUT}) $\pm\,$ 25 mA DC V_{CC}/GND Current (I_{CC}) \pm 75 mA Storage Temperature (T_{STG}) -65°C to $+150^{\circ}\text{C}$ Lead Temperature (T_L)

(Soldering, 10 seconds)

Note 1: Absolute Maximum Ratings are values beyond which the device may be damaged or have its useful life impaired. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation outside databook specifications.

Recommended Operating Conditions

Supply Voltage (V_{CC}) 2.0V to +5.5V Input Voltage (V_{IN}) 0V to +5.5VOutput Voltage (V_{OUT}) 0V to V_{CC} -40°C to +85°C Operating Temperature (T_{OPR}) Input Rise and Fall Time (t_r, t_f)

 $V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$ 0 ~ 100 ns/V 0 ~ 20 ns/V

DC Characteristics for 'VHC Family Devices

			74VHC							
Symbol	Parameter	V _{CC} (V)	т,	4 = 25°	°C		-40°C ⊢85°C	Units	Conditions	
			Min	Тур	Max	Min	Max	0 31		
V _{IH}	High Level Input Voltage	2.0 3.0-5.5	1.50 0.7 V _{CC}			1.50 0.7 V _{CC}	x 3	٧	S	
V_{IL}	Low Level Input Voltage	2.0 3.0-5.5			0.50 0.3 V _{CC}		0.50 0.3 V _{CC}	V		
V _{OH}	High Level Output Voltage	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -50 \mu A$
		3.0 4.5	2.58 3.94			2.48 3.80		V		$I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$
V _{OL}	Low Level Output Voltage	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 50 \mu A$
		3.0 4.5			0.36 0.36		0.44 0.44	V		$I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$
l _{OZ}	TRI-STATE Output Off-State Current	5.5			±0.25		±2.5	μΑ	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	
I _{IN}	Input Leakage Current	0-5.5			±0.1		±1.0	μΑ	$V_{IN} = 5.5V$ or GND	
I _{CC}	Quiescent Supply Current	5.5			4.0		40.0	μΑ	$V_{IN} = V_{CC}$ or GND	

260°C

Symbol		V _{CC} (V)	74	VHC	Units	Conditions
	Parameter		T _A =	= 25°C		
			Тур	Limits		
V _{OLP} **	Quiet Output Maximum Dynamic V _{OL}	5.0	0.9	1.2	٧	C _L = 50 pl
V _{OLV} **	Quiet Output Minimum Dynamic V _{OL}	5.0	-0.8	-1.0	٧	C _L = 50 pl
V _{IHD} **	Minimum High Level Dynamic Input Voltage	5.0		3.5	٧	C _L = 50 pF
V _{ILD} **	Maximum High Level Dynamic Input Voltage	5.0		1.5	٧	C _L = 50 pF

^{**}Parameter guaranteed by design.



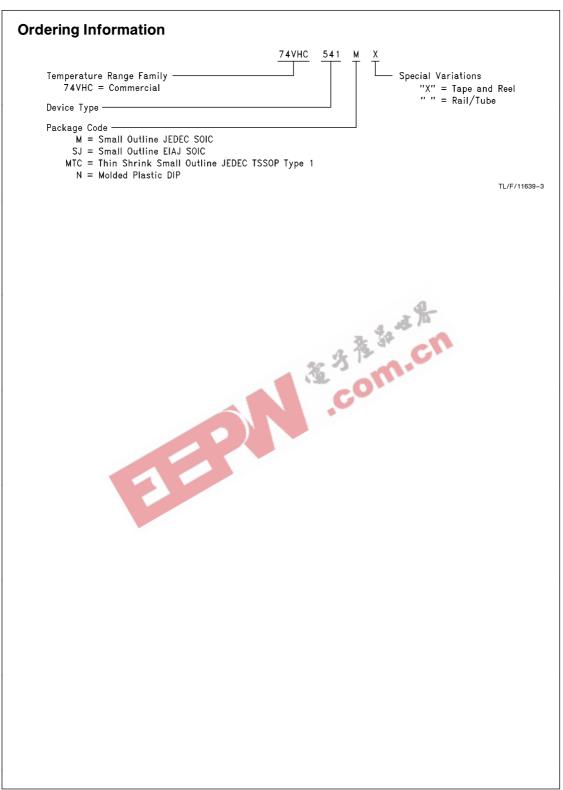
			74VHC		74VHC					
Symbol	Parameter	V _{CC} (V)	T,	_A = 25	°C		−40°C 85°C	Units	Conc	litions
			Min	Тур	Max	Min	Max			
t _{PLH} ,	Propagation Delay Time	3.3 ±0.3		5.0	7.0	1.0	8.5	ns		$C_L = 15 pF$
t _{PHL}		0.0 ± 0.0		7.5	10.5	1.0	12.0	115		$C_L = 50 pF$
		5.0 ±0.5		3.5	5.0	1.0	6.0	ns		$C_L = 15 pF$
		0.0 _ 0.0		5.0	7.0	1.0	8.0			$C_L = 50 pF$
t_{PZL} ,	TRI-STATE Output Enable Time	3.3 ± 0.3		6.8	10.5	1.0	12.5	ns	$R_L = 1 k\Omega$	$C_L = 15 pF$
t _{PZH}		0.0 = 0.0		9.3	14.0	1.0	16.0			$C_L = 50 pF$
		5.0 ± 0.5		4.7	7.2	1.0	8.5	ns		$C_L = 15 pF$
		0.0 = 0.0		6.2	9.2	1.0	10.5	115		$C_L = 50 pF$
t_{PLZ} ,	TRI-STATE	3.3 ± 0.3		11.2	15.4	1.0	17.5		$R_L = 1 k\Omega$	$C_L = 50 pF$
t_{PHZ}	Output Disable Time	5.0 ±0.5		6.0	8.8	1.0	10.0	ns		C _L = 50 pF
toslh,	Output to Output Skew	3.3 ±0.3			1.5		1.5		(Note 1)	$C_L = 50 pF$
toshl		5.0 ±0.5			1.0		1.0	ns	2 /5	$C_L = 50 \text{ pF}$
C _{IN}	Input Capacitance			4	10		10	рF	V _{CC} = Oper	ı
C _{OUT}	Output Capacitance			6			12 1	pF	$V_{CC} = 5.0V$	
						200		-		

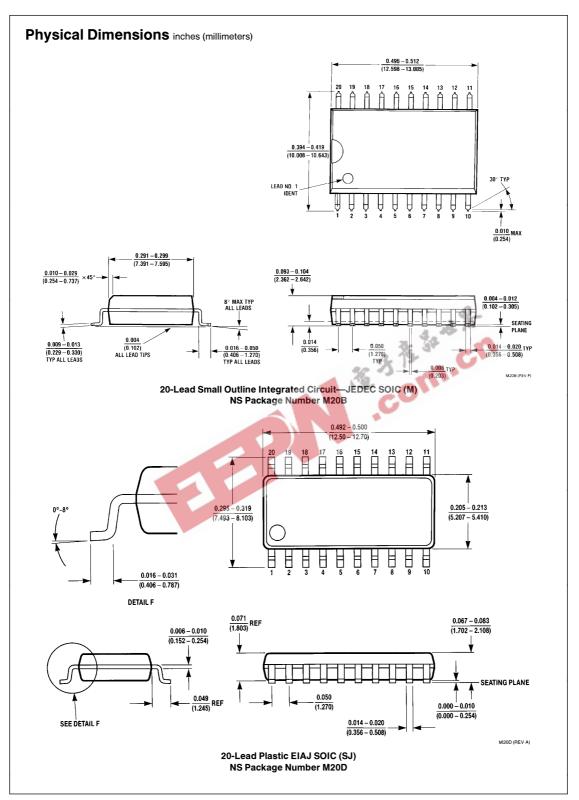
Power Dissipation Capacitance

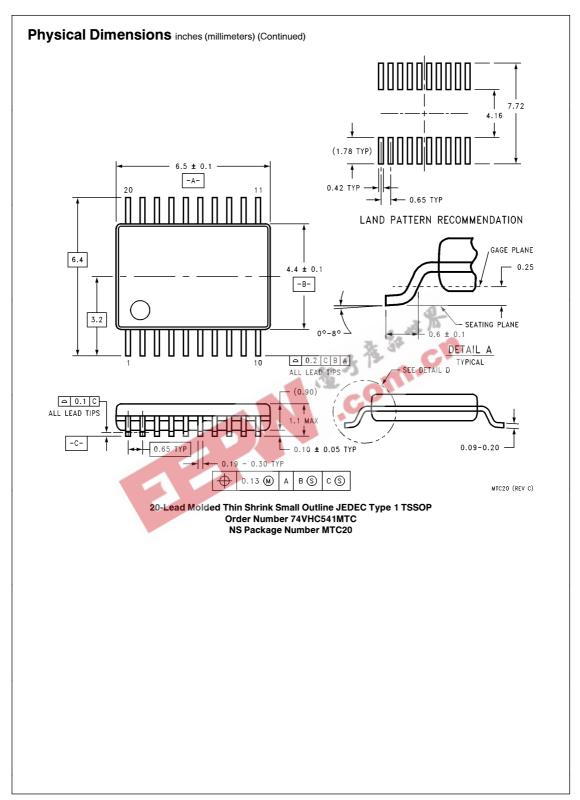
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Note 1: Parameter guaranteed by design. to SLH = |tpLHmax - tpLHmin|; to SHL = |tpHLmax - tpHLmin|.

Note 2: CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: |CC (OPR.) = CpD * Vcc |f|_N + |CC|_B (per bit).







Physical Dimensions millimeters (Continued) (25.73-26.42) 0.092×0.030 (2.337 × 0.762) 0.032 ±0.005 20 19 18 17 16 15 14 13 12 11 (0.813±0.127) RAD 0.260 ±0.005 PIN NO. 1 IDENT (6.604 ±0.127) PIN NO. 1 IDENT 0.280 (7,112) 1 2 3 4 5 6 7 8 9 10 0.090 OPTION 2 0.300-0.320 -(2.286)(7.620-8.128) 0.060 NOM 0.040 OPTION 2 4° (4X) 0.130 0.005 (1.524) TYP (1.016) TYP 0.065 (3.302 0.127) (1.651) 0.145-0.200 (3.683-5.080) 90°± 0.004° 0.009-0.015 0.020 (0.229-0.381) 0.100 ± 0.010 0.125-0.140 (3.175-3.556) (0.508) MIN TYP 0.060 ± 0.005 (2.540 ± 0.254) 0.018 ± 0.003 0.325 +0.040 -0.015 (1.524 ± 0.127) (0.457 ± 0.076) 8.255 +1.016 -0.381 20-Lead (0.300" Wide) Molded Dual-In-Line Package Order Number 74VHC541N NS Package Number N20A

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National Semiconductor Corporation 1111 West Bardin Road Arlington, TX 76017 Tel: 1(800) 272-9959 Fax: 1(800) 737-7018

National Semiconductor Europe

Europe Fax: (+49) 0-180-530 85 86
Email: cnjwge@tevm2.nsc.com
Deutsch Tel: (+49) 0-180-530 85 85
English Tel: (+49) 0-180-532 78 32
Français Tel: (+49) 0-180-532 33 18
Italiano Tel: (+49) 0-180-534 16 80

National Semiconductor Hong Kong Ltd. 13th Floor, Straight Block, Ocean Centre, 5 Canton Rd. Tsimshatsui, Kowloon Hong Kong Tei: (852) 2737-1600 Fax: (852) 2736-9960

National Semiconductor Japan Ltd. Tel: 81-043-299-2309